

IN THE ABSTRACT

Please replace the Abstract with the attached revised Abstract located at the end of this document.

ABSTRACT OF THE DISCLOSURE

A nitride-based semiconductor light-emitting device having excellent reliability and long lifetime, and a method of manufacturing the same are provided. A nitride-based semiconductor light-emitting element chip, in which a nitride-based semiconductor layer and a first electrode are formed on a surface of an electrically conductive substrate and a second electrode is formed on a rear surface of the electrically conductive substrate, is mounted on a submount, and the submount having the nitride-based semiconductor light-emitting element chip mounted thereon is further mounted on a stem to form a nitride-based semiconductor light-emitting device.